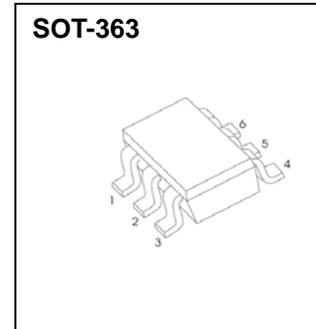
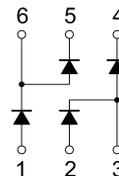


## Plastic-Encapsulate Diodes

SWITCHING DIODE

### FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance



MAKING: KGJ

### Maximum Ratings @Ta=25°C

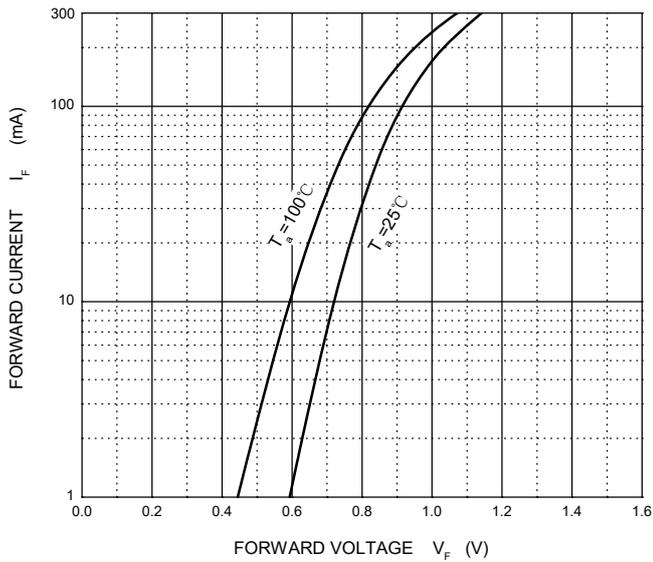
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	75	V
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output Current	$I_O$	150	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	2 1	A
		@ t = 1.0µs @ t = 1.0s	
Power Dissipation	$P_D$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

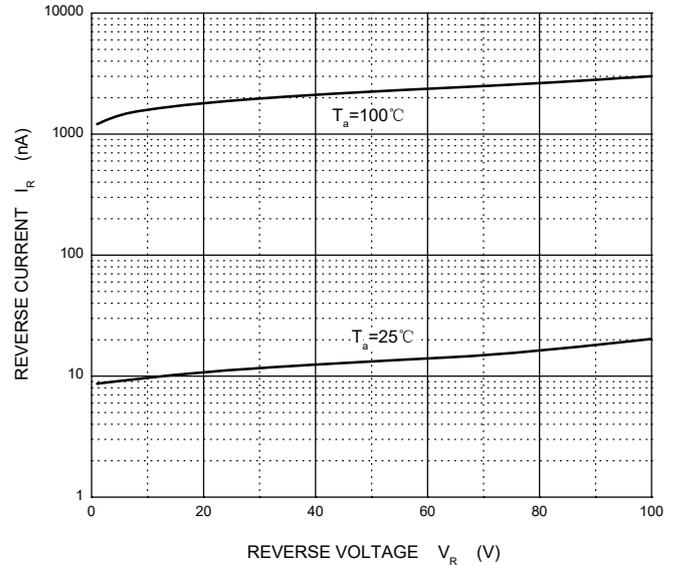
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 10\mu A$	75		V
Reverse voltage leakage current	$I_R$	$V_R = 75V$ $V_R = 20V$		2.5 0.025	µA
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Junction capacitance	$C_T$	$V_R = 0, f = 1MHz$		2	pF
Revers recovery time	$t_{rr}$	$I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R,$ $R_L = 100\Omega$		4	ns

## Typical Characteristics

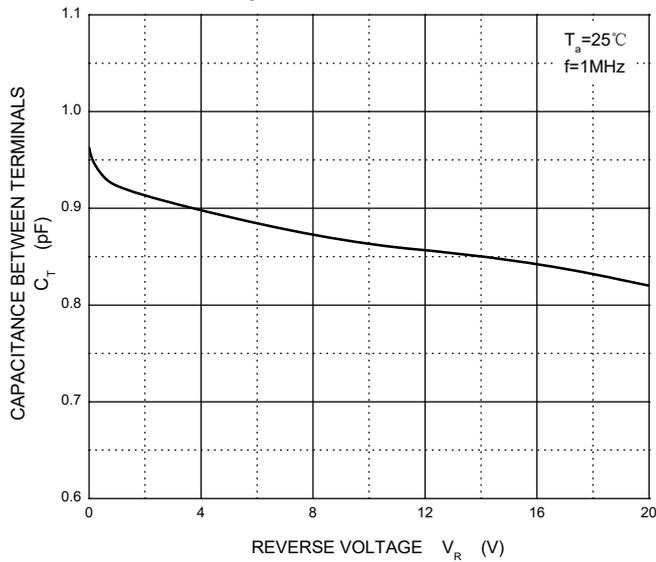
**Forward Characteristics**



**Reverse Characteristics**



**Capacitance Characteristics**



**Power Derating Curve**

